Silicon NPN transistor in a TO-92 Plastic Package.

V_{CEO}< 80V.(I_C =1mA).

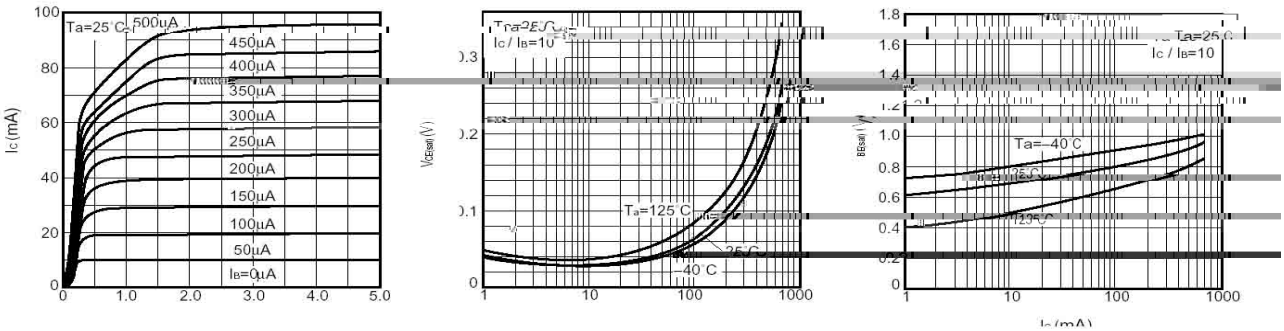
/ Absolute Maximum Ratings(Ta=25)

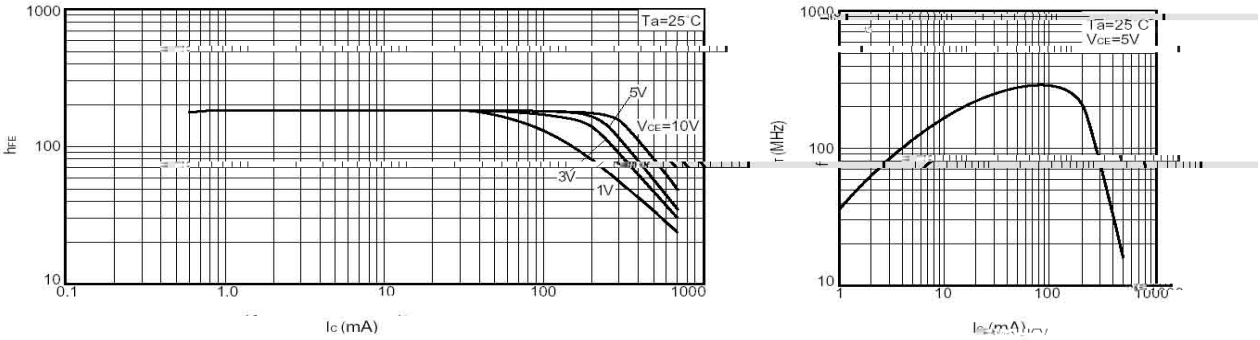
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	500	mA
Peak Collector Current	I_{CM}	1	A
Peak Base Current	I_{BM}	200	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

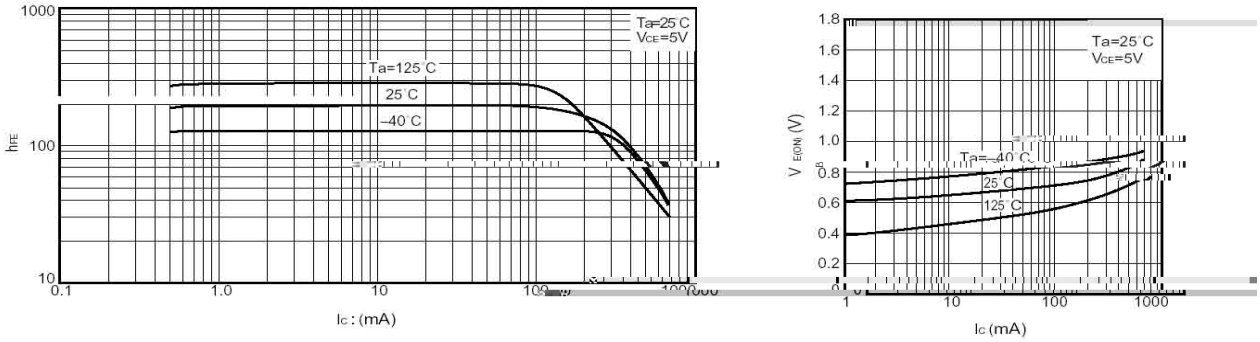
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=80V I_E=0			0.05	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5 I_C=0			0.05	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=1V I_C=100mA	100			
	$h_{FE(2)}$	V_{CE}=1V I_C=10mA	100			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA I_B=10mA			0.25	V
Base to Emitter Voltage	V_{BE}	V_{CE}=1V I_C=100mA			1.2	V
Transition Frequency	f_T	V_{CE}=2V I_C=10mA f=100MHz	100			MHz

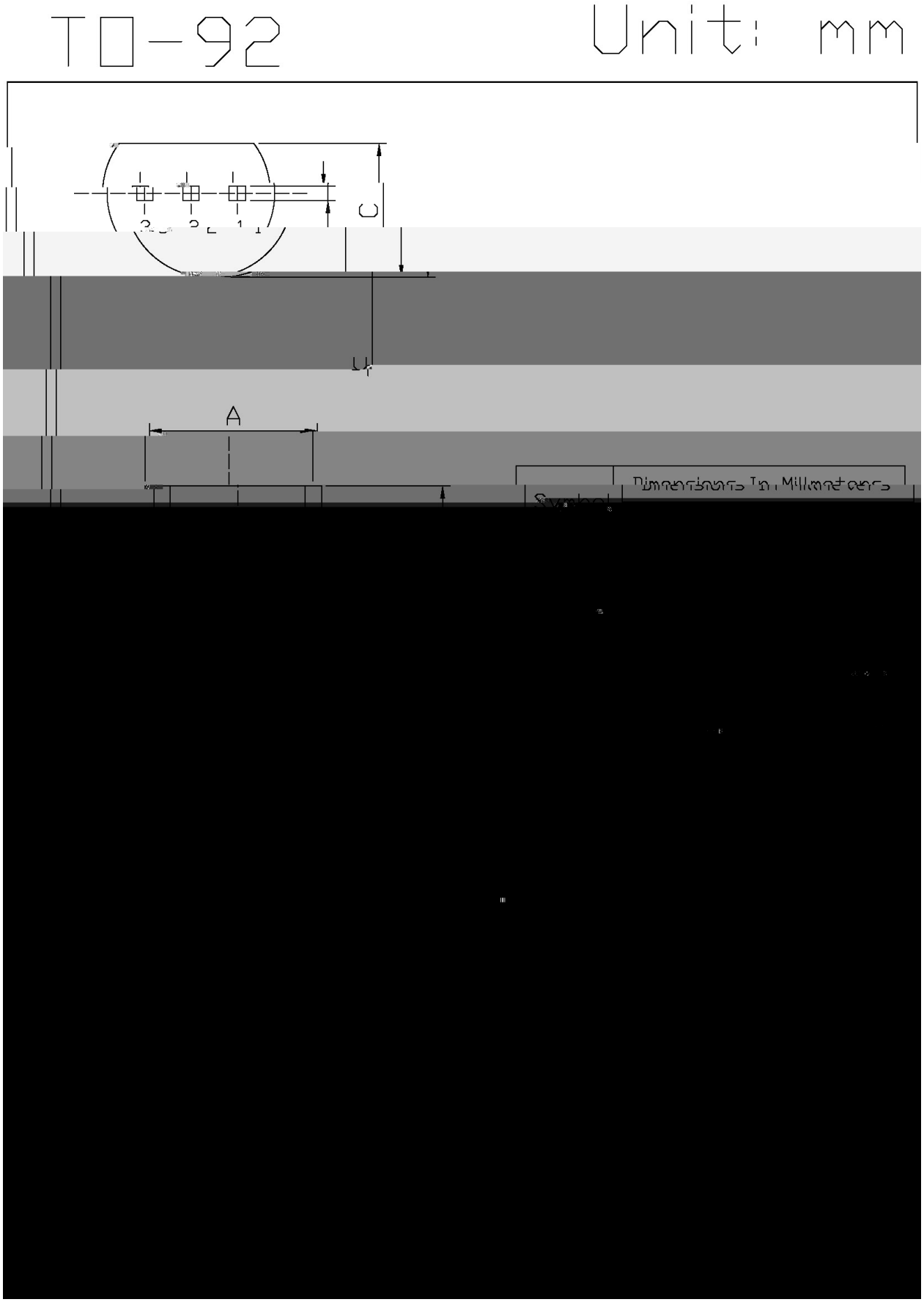
/ Electrical Characteristic Curve



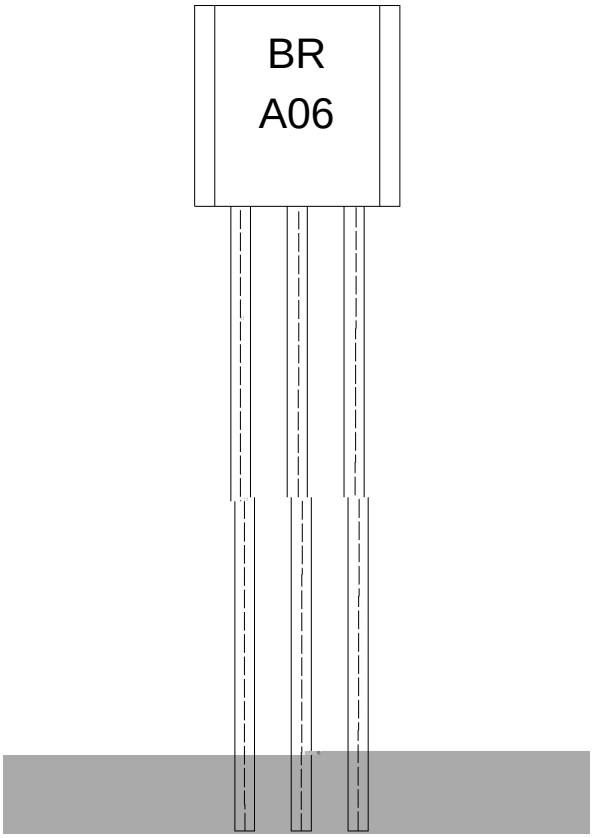




/ Package Dimensions



/ Marking Instructions



Note:

BR:	Company Code.
A06:	Product Type.
****:	Lot No. Code,code change with Lot No.